

Abstract of the Disclosure

Disclosed is a method for forming metal lines, which comprises the following steps of: preparing a semiconductor substrate having a lower metal line; successively forming a polymer dielectric film and an oxide film on the substrate, the polymer dielectric film and the oxide film having a contact for exposing a predetermined portion of the lower metal line; dry cleaning a resultant structure according to a remote plasma mechanism to remove the metal oxide film from the surface portion of the lower metal line exposed via the contact and to form a protective film on a lateral portion of the polymer dielectric film; and embedding a metal film functioning as an upper metal line in a contact structure.